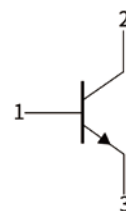


Features

- Epitaxial planar die construction
- Complementary PNP Type available(PXT2907A)



SOT-89-3L



Equivalent Circuit

Absolute Maximum Ratings(T_A=25℃)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	75	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	0.6	A
P _C	Collector Power Dissipation	0.5	W
T _J , T _{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	℃

Electrical Characteristics (T_A=25℃ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =10μA, I _E =0	75			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA, I _B =0	40			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10μA, I _C =0	6			V
I _{CBO}	Collector cut-off current	V _{CB} =60V, I _E =0			0.01	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V, I _C =0			0.01	μA
h _{FE(1)}	DC current gain	V _{CE} =10V, I _C =0.1mA	35			
h _{FE(2)}		V _{CE} =10V, I _C =1mA	50			
h _{FE(3)}		V _{CE} =10V, I _C =10mA	75			
h _{FE(4)}		V _{CE} =10V, I _C =150mA	100		300	
h _{FE(5)}		V _{CE} =1V, I _C =150mA	50			
h _{FE(6)}		V _{CE} =10V, I _C =500mA	40			
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =500mA, I _B =50mA			1	V
V _{CE(sat)}		I _C =150mA, I _B =15mA			0.3	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =500mA, I _B =50mA			2.0	V
V _{BE(sat)}		I _C =150mA, I _B =15mA	0.6		1.2	V
f _T	Transition frequency	V _{CE} =10V, I _C =20mA, f=100MHz	300			MHz
C _{ob}	Collector output capacitance	V _{CB} =10V, I _E =0, f=1MHz			8	pF
t _d	Delay time	V _{CC} =30V, I _C =150mA V _{BE(off)} =0.5V, I _{B1} =15mA			10	ns
t _r	Rise time				25	ns
t _s	Storage time	V _{CC} =30V, I _C =150mA I _{B1} =- I _{B2} =15mA			225	ns
t _f	Fall time				60	ns

Ordering information

Product ID	Pack	Naming rule	Marking	hFE(1)	Qty(PCS)
PXT2222A	SOT-89-3L	PXT2222A 产品名称 product name	1P	100-300	1000



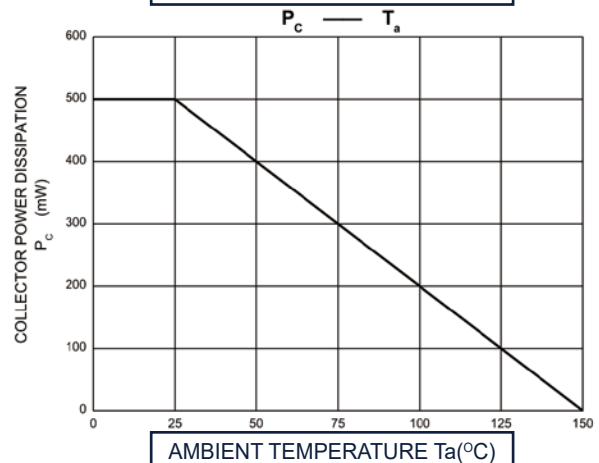
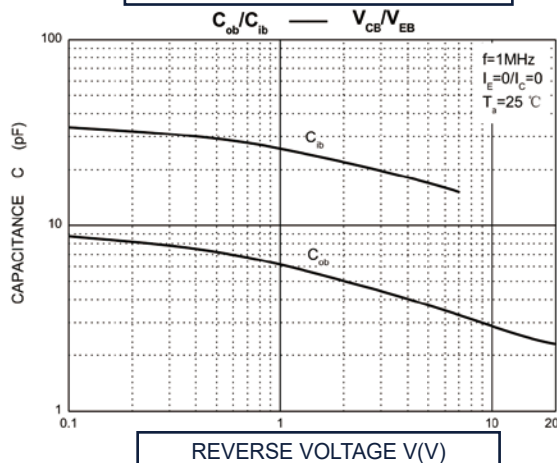
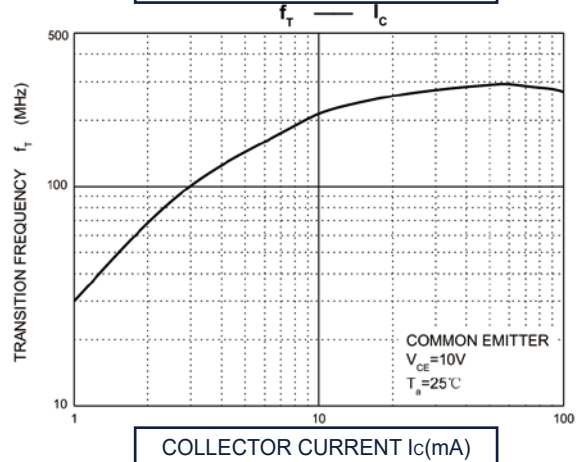
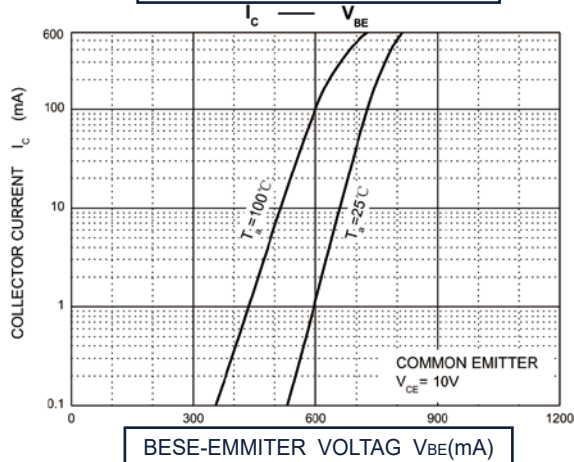
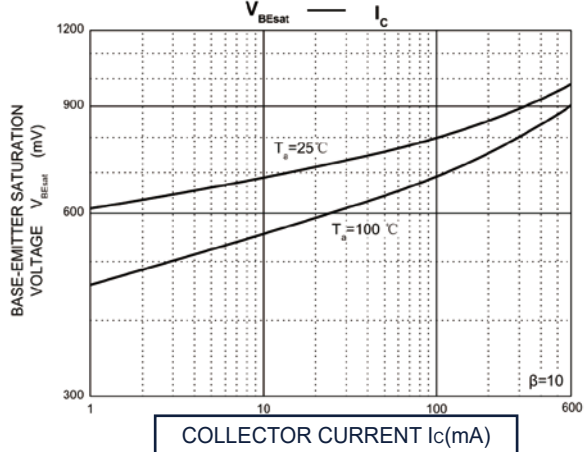
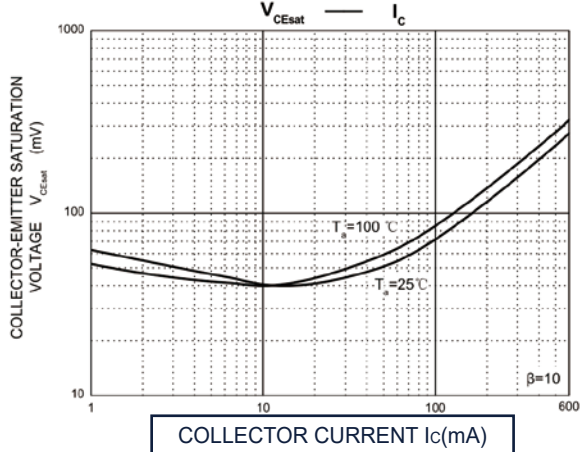
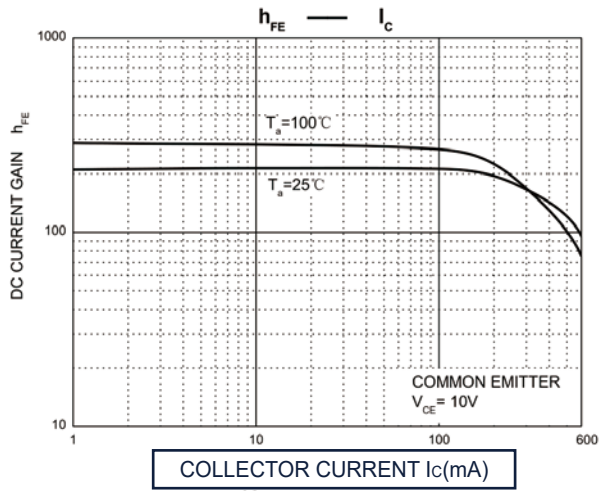
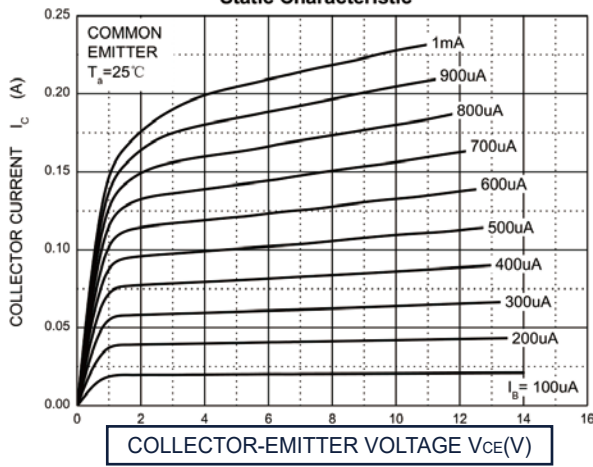
TWTLSEMI

TL-PXT2222A

SOT-89-3L Plastic-Encapsulate Transistors (NPN)

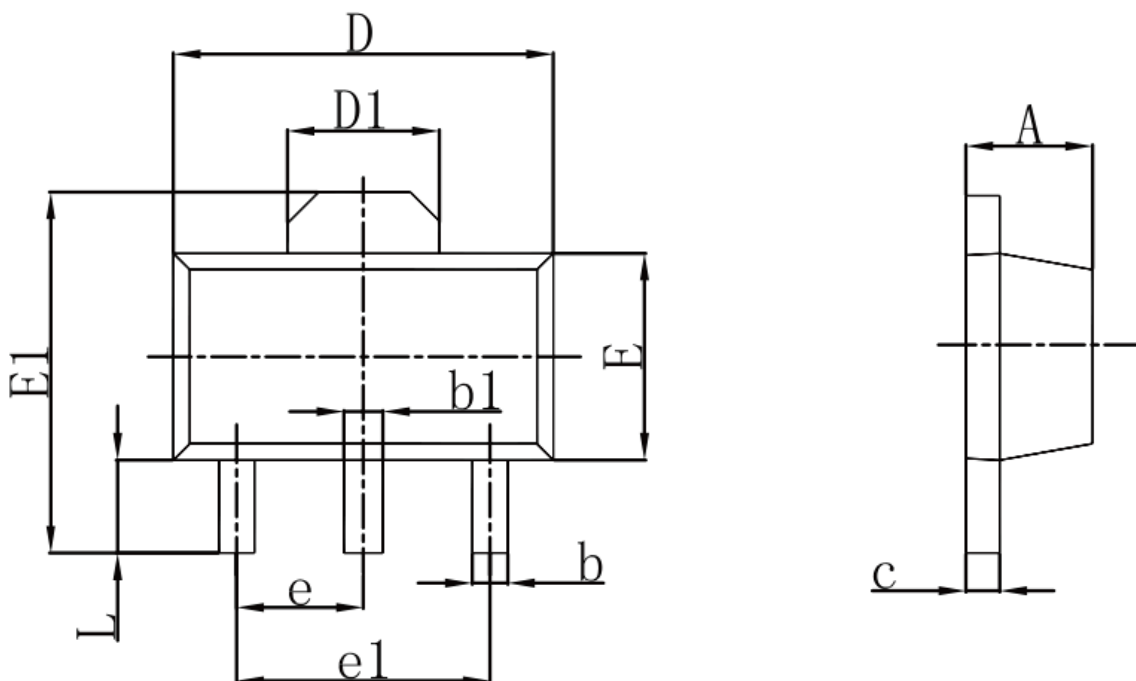
Typical Characteristics

Static Characteristic





SOT-89-3L Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047